

chamber, for receiving a wafer thereon;

means for annealing the wafer, said means being installed at an upper portion of the processing chamber; and

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cut a gas diffuser installed below the wafer annealing means, for supplying reaction gases into the process chamber.

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B2 11. (Amended) The semiconductor manufacturing apparatus of claim 7, wherein the wafer annealing means is one of a lamp and a laser.

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38. (Amended) A semiconductor manufacturing apparatus, comprising:  
a vertically movable susceptor installed at a lower portion of a processing chamber and adapted to support a wafer thereon;

B3 a heater which anneals the wafer, said heater being disposed within an upper portion of the processing chamber above the susceptor; and  
a gas diffuser installed within the processing chamber and adapted to supply reaction gases into the process chamber.

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Please cancel claim 42 without prejudice or disclaimer thereof..

Please add the following new claims 44-49.

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B4 -- 44. A semiconductor manufacturing apparatus, comprising:  
a processing chamber;

a vertically movable susceptor installed at a lower portion of the processing chamber and adapted to support a wafer thereon;

means for annealing a wafer, said means being disposed within an upper portion of the processing chamber above the susceptor; and

gas diffusing means for diffusing at least one process gas into the process chamber, said diffusing means being installed within the processing chamber.

45. The apparatus of claim 44, wherein the gas diffusing means is connected to two separate pipes extending outside of processing chamber, one of the two pipes being adapted to supply to the gas diffusing means a first gas excited to a plasma state and another of the two pipes being adapted to supply to the gas diffusing means a second gas that is in a non-plasma state.

46. The apparatus of claim 45, further comprising a plasma generating device for exciting the first gas into the plasma state.

47. The apparatus of claim 44, wherein the means for annealing the wafer is one of a lamp and a laser.

48. The apparatus of claim 44, wherein the susceptor has therein a cooling line adapted to control a temperature of the wafer